

Amendments to the Specification:

Page 7, lines 1-8: Replace paragraph [019] of the original specification with the following new paragraph [019]:

[019] Floating gate 112 may be formed with conventional chemical vapor deposition (CVD) method using a combination of gases that is comprised of a reaction gas and an optional second gas. In one aspect, the reaction gas is comprised of SiX , Si_2Y , or any appropriate combination thereof, wherein X is comprised of one or more of H_4 , H_2Cl_2 , HCl_3 , D_4 , D_2Cl_2 , and D_3Cl , and Y is comprised of one or more of ~~H₆~~ H_6 , H_4Cl_2 , H_2Cl_4 , D_6 , D_4Cl_2 , and D_2Cl_4 . In another aspect, the optional second gas is comprised of at least one or more of D_2 , H_2 , and D_3 .